# PROCESS CP191V

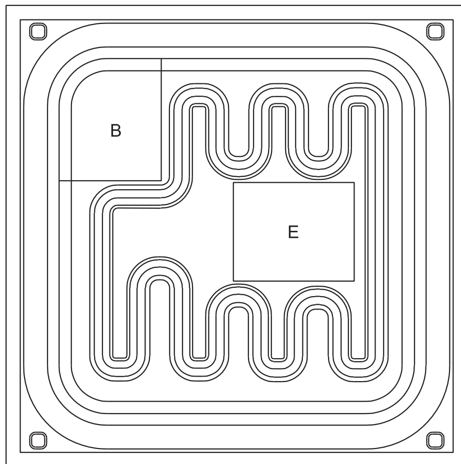
## Small Signal Transistor

### NPN - Amp/Switch Transistor Chip

### PROCESS DETAILS

| Process | EPITAXIAL PLANAR |
|---|---|
| Die Size | 16.5 x 16.5 MILS |
| Die Thickness | 7.1 MILS |
| Base Bonding Pad Area | 3.5 x 4.3 MILS |
| Emitter Bonding Pad Area | 3.5 x 4.3 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au-As - 13,000Å |

### GEOMETRY




BACKSIDE COLLECTOR R3

**GROSS DIE PER 4 INCH WAFER**
**41,699**

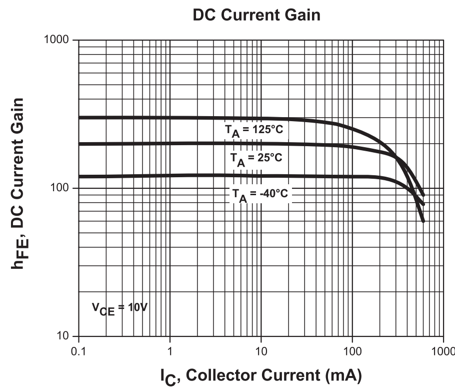
**PRINCIPAL DEVICE TYPES**

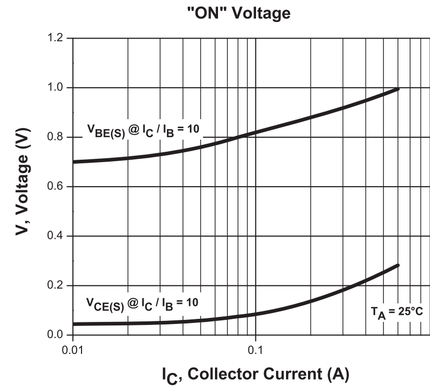
CMLT2222A
CMLT2207
CMLM2205
CMKT2207

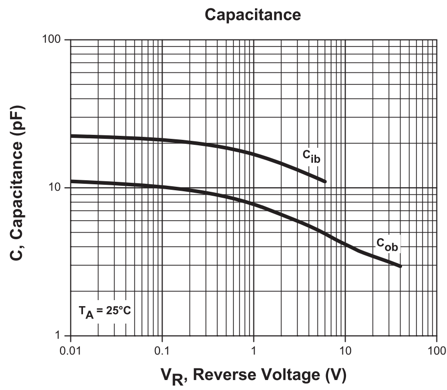
R1 (22-March 2010)

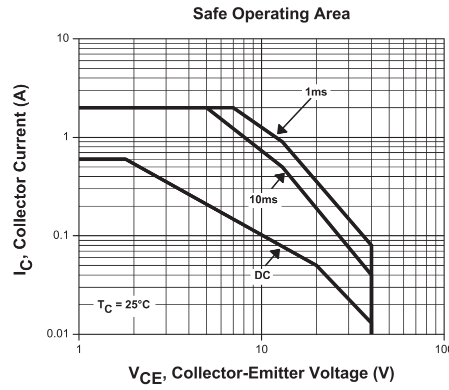
# PROCESS CP191V

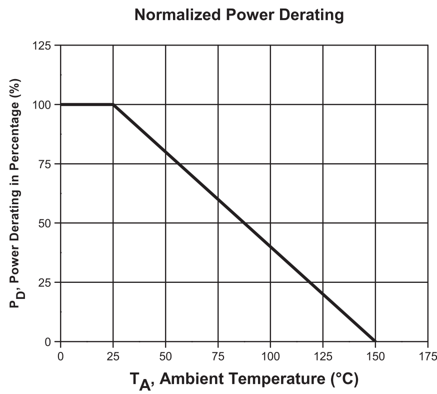
## Typical Electrical Characteristics

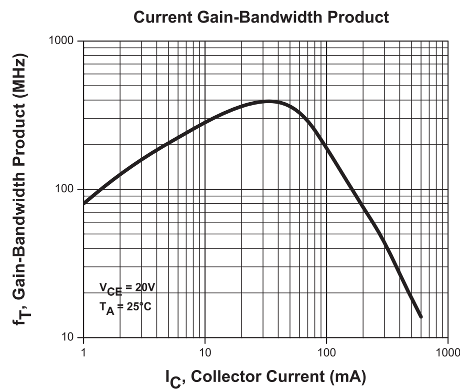



R1 (22-March 2010)